

SSC8125GS6

P-Channel Enhancement Mode MOSFET with ESD Protection

> Features

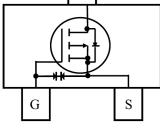
VDS	VGS	RDSON Typ.	ID	ESD
-20V	±8V	36mR@-4V5	-4A	3kV
		45mR@-2V5		
		57mR@-1V8		
		66mR@-1V5		

> Description

This device uses advanced trench technology to provide excellent RDSON, low gate charge and operation with gate voltages as low as 1.5V and it is protected from ESD. These features make it suitable for use as a load switch or in PWM applications.

3kV

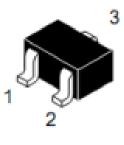
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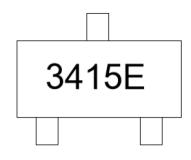
Top view

D

Pin configuration



SOT23



Marking

> Applications

- Load Switch
- Portable Devices
- DCDC conversion

> Ordering Information

Device	Package	Shipping		
SSC8125GS6	SOT23	3000/Reel		



> Absolute Maximum Ratings(T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V _{DSS}	Drain-to-Source Voltage	-20	V
V _{GSS}	Gate-to-Source Voltage	±8	V
۱ _D	Continuous Drain Current ^a	-4	А
I _{DM}	Pulsed Drain Current ^b	-20	А
P _D	Power Dissipation ^c	0.9	W
P _{DSM}	Power Dissipation ^a	0.45	W
TJ	Operation junction temperature	-55 to 150	°C
T _{STG}	Storage temperature range	-55 to 150	°C

> Thermal Resistance Ratings($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance		280	°C /\AI
R _{θJC}	Junction-to-Case Thermal Resistance		140	°C/W

Note:

- a. The value of RθJA is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with TA=25°C.The value in any given application depends on the user is specific board design. The current rating is based on the t≤ 10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation PD is based on TJ(MAX)=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

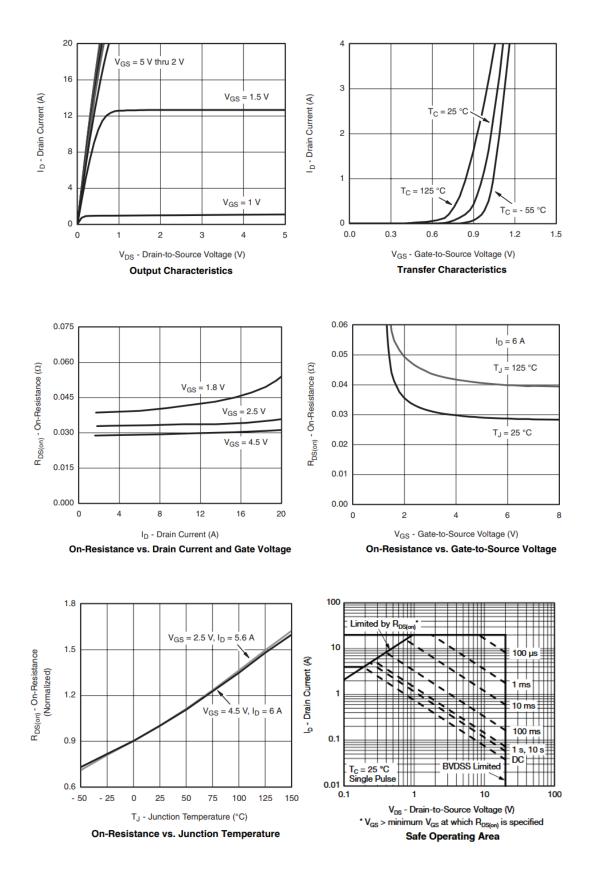


Electronics Characteristics(T_A=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V , ID=-250uA	-20			V
$V_{GS \ (th)}$	Gate Threshold Voltage	VDS=VGS , ID=-250uA	-0.4	-0.6	-0.9	V
		VGS=-4.5V , ID=-4A		36	41	
В	Drain-Source On-	VGS=-2.5V , ID=-3A		45	52	mR
R _{DS(on)}	Resistance	VGS=-1.8V , ID=-2A		57	62	
		VGS=-1.5V , ID=-1A		66	72	
I _{DSS}	Zero Gate Voltage Drain Current	VDS=-20V , VGS=0V			-1	uA
I _{GSS}	Gate-Source leak current	VGS=±8V , VDS=0V			±10	uA
G _{FS}	Transconductance	VDS=-5V , ID=-4A		16		S
V_{SD}	Forward Voltage	VGS=0V , IS=-1.6A		-0.7	-1.3	V
Ciss	Input Capacitance			418		
Coss	Output Capacitance	VDS=-10V, VGS=0V, F=1MHZ		136		pF
Crss	Reverse Transfer Capacitance			56		
T _{D(ON)}	Turn-on delay time			18		
Tr	Rise time	VGS=-5V,		12		
T _{D(OFF)}	Turn-off delay time	VDS=-10V, RL=1.5R, RG=3R		70		ns
Tf	Fall time			25		

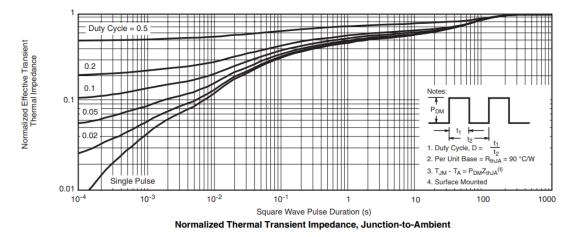


> Typical Characteristics(T_A=25°C unless otherwise noted)



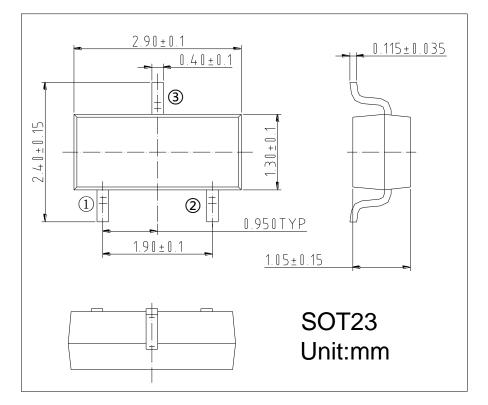


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Package Information



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